

EAST - [jig.wsp:1]

FileViewEditIconsWindowHelp

Drafts

Pending

Active

L1: (21245) flash and (memory or memories) and gate

L2: (944) 1 and (split adj gate)

L3: (909) 2 and ((control adj gate) or (floating adj gate))

L4: (444) 3 and spacer\$1

L5: (342) 4 and (control adj gate) and (floating adj gate)

L6: (369) 5 and ((source or drain) or (source adj drain))

L7: (376) 6 and gate.clm.

L8: (367) 7 and etch\$2

L9: (344) 8 and (mask or photoresist)

L10: (154) 9 and (select\$2 adj gate)

L11: (103) 10 and spacer\$1.clm.

BrowseQueueClear

DBs:USPA:USCPUB

Default operator:OR

11 and (select\$2 adj gate).clm.

Full ScreenLeft PaneRight PaneTextHTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	3	Ir
26	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6096603 A	20000801	11	Method of fabricating a split gate structure of a fl	438/258	257/221.638; 438/266		Chang, Ko-Hsing et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
27	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6005607 A	19991221	9	Method and apparatus for self-aligned memory cells an	365/185.26	257/221.422; 257/227.103;		Chen, Bin-Shing	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
28	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5965960 A	19991123	33	Semiconductor device and method for fabricating the s	438/267	257/221.682; 257/227.103;		Fukase, Kenji	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
29	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5943261 A	19990624	16	Method for programming a flash memory	365/185.14	257/221.422; 257/229.129;		Lee, William W. Y.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
30	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5939749 A	19990817	23	Split gate transistor array	257/316	257/319; 257/909;		Taketa, Kaoru et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
31	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5796139 A	19980818	31	Semiconductor device	257/315	257/316; 257/221.632;		Fukase, Kenji	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
32	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5793079 A	19980811	21	Single transistor non-volatile electrically al	257/316	257/315; 257/320;		Georgescu, Scrin et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
33	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5702965 A	19971230	7	Flash memory cell and method of making the same	438/261	257/221.422; 257/229.129;		Kim, Jeoung Woo	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
34	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5614747 A	19970325	13	Method for manufacturing a flash EEPROM cell	257/316	257/319; 257/321;		Ahn, Byung J. et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
35	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5554869 A	19960910	3	Electrically programmable read-only memory array	257/316	257/325; 257/933;		Chang, Kuo-Tung	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
36	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5494838 A	19960227	10	Process of making EEPROM memory device having a sidew	438/264	257/227.103; 257/229.129;		Chang, Kuo-Tung et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
37	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5467308 A	19951114	11	Cross-point eeprom memory array	365/185.01	257/314; 257/316;		Chang, Kuo-Tung et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
38	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5455792 A	19951003	21	Flash EEPROM devices employing mid channel inject	365/185.15	257/316; 257/319;		Yi, Yong-Wan	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
39	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5422504 A	19950606	12	EEPROM memory device having a sidewall spacer floating g	365/185.15	257/315; 257/321;		Chang, Kuo-Tung et al.	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US
40	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 5408115 A	19950416	9	Self-aligned, split-gate EEPROM device	257/324	257/314; 257/325;		Chang, Kuo-Tung	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US

Ready

NUM